

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/035,503
Applicant: Katsuji Iguchi *et al.*
Filed: October 25, 2001
Group #: 2812
Examiner: Christopher W. Lattin

Confirmation Number: 3213

Docket No: SLA.0636
Customer No: 27518
For: METHOD OF FABRICATING DEEP SUB-MICRON CMOS SOURCE/DRAIN
WITH MDD AND SELECTIVE CVD SILICIDE

MS RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

PRELIMINARY AMENDMENT IN SUPPORT OF RCE UNDER 37 C.F.R. § 1.114
Introductory Comments

In response to the Office Action dated July 23, 2003, please amend the above-identified Application as follows:

Amendment to the Specification None

Amendment to the Claims are reflected in the listing of claims which begins on page 2, of this paper.

Amendment to the Drawings None

Remarks/Arguments begin on page 8 of this paper.

An Appendix is not included.

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